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MPPS™ Miniature Package Power Solutions DUAL 12V PNP LOW SATURATION SWITCHING TRANSISTOR

SUMMARY

 V_{CEO} = -12V; R_{SAT} = 60m Ω ; I_{C} = -4A

DESCRIPTION

Packaged in the innovative 3mm x 2mm MLP (Micro Leaded Package) outline, these new 4th generation low saturation dual transistors offer extremely low on state losses making them ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users gain several other key benefits:

Performance capability equivalent to much larger packages

Improved circuit efficiency & power levels

PCB area and device placement savings

Lower package height (nom 0.9mm)

Reduced component count

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (-140mV @ -1A)
- hFF characterised up to -10A
- I_C = -4A Continuous Collector Current
- 3mm x 2mm MLP

APPLICATIONS

- DC DC Converters (FET Drivers)
- Charging circuits
- Power switches
- Motor control

ORDERING INFORMATION

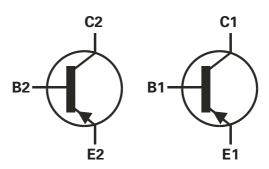
<u> </u>								
DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL					
ZXTD1M832TA	7′′	8mm	3000					
ZXTD1M832TC	13′′	8mm	10000					

DEVICE MARKING

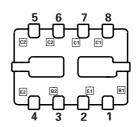
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3mm x 2mm (Dual die) MLP



PINOUT



3mm x 2mm MLP underside view



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-12	V
Emitter-Base Voltage	V _{EBO}	-7.5	V
Peak Pulse Current	I _{CM}	-12	A
Continuous Collector Current	I _C	-4	A
Continuous Collector Current (b)	I _C	-4.4	A
Base Current	I _B	-1000	mA
Power Dissipation at TA=25°C (a)(f) Linear Derating Factor	P _D	1.5 12	W mW/°C
Power Dissipation at TA=25°C (b)(f) Linear Derating Factor	P _D	2.45 19.6	W mW/°C
Power Dissipation at TA=25°C (c)(f) Linear Derating Factor	P _D	1 8	W mW/°C
Power Dissipation at TA=25°C (d)(f) Linear Derating Factor	P _D	1.13 9	W mW/°C
Power Dissipation at TA=25°C (d)(g) Linear Derating Factor	P _D	1.7 13.6	W mW/°C
Power Dissipation at TA=25°C (e)(g) Linear Derating Factor	P _D	3 24	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	°C/W
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	°C/W
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	°C/W
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	°C/W
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	°C/W
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	°C/W

Notes

(a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions with all exposed pads attached. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(b) Measured at t<5 secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions with all exposed pads attached. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions with minimal lead connections only.

(d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions with all exposed pads attached attached. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions with all exposed pads attached attached. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(f) For a dual device with one active die.

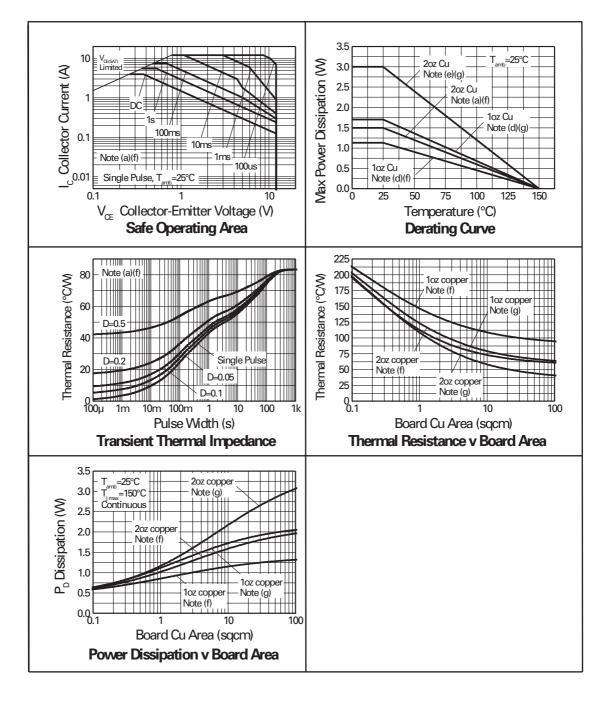
(g) For dual device with 2 active die running at equal power.

(h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.

(i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is Rth = 250°C/W giving a power rating of Ptot = 500mW.



TYPICAL CHARACTERISTICS





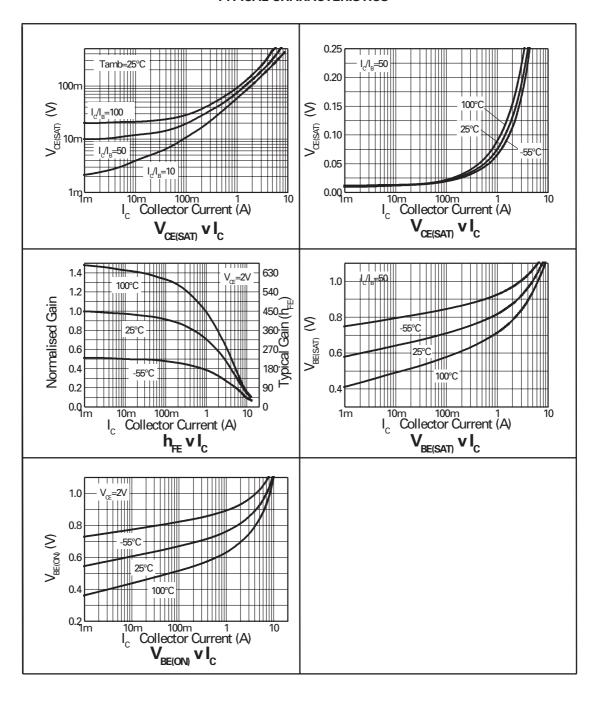
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

W1110							
SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.		
V _{(BR)CBO}	-20	-35		V	I _C =-100μA		
V _{(BR)CEO}	-12	-25		V	I _C =-10mA*		
V _{(BR)EBO}	-7.5	8.5		V	I _E =-100μA		
I _{CBO}			-25	nA	V _{CB} =-16V		
I _{EBO}			-25	nA	V _{EB} =-6V		
I _{CES}			-25	nA	V _{CES} =-10V		
V _{CE(sat)}		-10	-17	mV	I _C =-0.1A, I _B =-10mA*		
		-100	-140	mV	I _C =-1A, I _B =-10mA*		
		-100	-150	mV	I _C =-1.5A, I _B =-50mA*		
		-195	-300	mV	I _C =-3A, I _B =-50mA*		
		-240	-300	mV	I _C =-4A, I _B =-150mA*		
V _{BE(sat)}		-0.97	-1.050	V	I _C =-4A, I _B =150mA*		
V _{BE(on)}		-0.87	-0.950	V	I _C =-4A, V _{CE} =-2V*		
h _{FE}	300	475			I _C =-10mA, V _{CE} =-2V*		
	300	450			I _C =-0.1A, V _{CE} =-2V*		
	180	275			I _C =-2.5A, V _{CE} =-2V*		
	60	100			I _C =-8A, V _{CE} =-2V*		
	45	70			I _C =-10A, V _{CE} =-2V*		
f _T	100	110		MHz	I _C =-50mA, V _{CE} =-10V f=100MHz		
C _{obo}		21	30	pF	V _{CB} =10V, f=1MHz		
t _(on)		70		ns	V _{CC} =-6V, I _C =-2A		
t _(off)		130		ns	I _{B1} =I _{B2} =-50mA		
	V(BR)CBO V(BR)CEO V(BR)EBO ICBO IEBO ICES VCE(sat) VBE(sat) FT Cobo t(on)	V(BR)CBO -20 V(BR)CEO -12 V(BR)EBO -7.5 ICBO IEBO ICES VCE(sat) VBE(sat) VBE(on) hFE 300 180 60 45 fT 100 Cobo t(on)	V(BR)CBO -20 -35 V(BR)CBO -12 -25 V(BR)EBO -7.5 8.5 ICBO IEBO ICES VCE(sat) -10 -100 -100 -195 -240 VBE(sat) -0.97 VBE(on) hFE 300 475 300 450 180 275 60 100 45 70 fT 100 110 Cobo 21 t(on) 70	V(BR)CBO -20 -35 V(BR)CEO -12 -25 V(BR)EBO -7.5 8.5 ICBO -25 ICES -25 VCE(sat) -10 -17 -100 -140 -100 -150 -195 -300 -240 -300 VBE(sat) -0.97 -1.050 VBE(on) -0.87 -0.950 hFE 300 475 300 450 180 275 60 100 45 70 fT 100 110 10 Cobo 21 30 t(on) 70 10	V(BR)CBO -20 -35 V V(BR)CEO -12 -25 V V(BR)EBO -7.5 8.5 V ICBO -25 nA ICES -25 nA VCE(sat) -10 -17 mV -100 -140 mV -195 -300 mV -195 -300 mV -240 -300 mV VBE(sat) -0.97 -1.050 V VBE(on) -0.87 -0.950 V hFE 300 475 450 180 275 60 100 45 70 MHz Cobo 21 30 pF t(on) 70 ns		

^{*}Measured under pulsed conditions. Pulse width=300 $\mu s.$ Duty cycle $\leq 2\%$



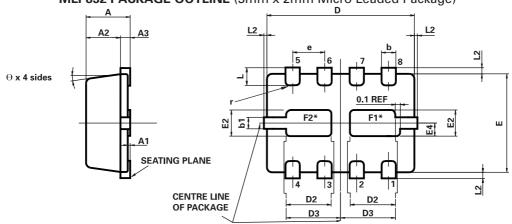
TYPICAL CHARACTERISTICS



ISSUE 1 - JUNE 2002



MLP832 PACKAGE OUTLINE (3mm x 2mm Micro Leaded Package)



*Exposed Flags. Solder connection to improve thermal dissipation is optional.

F1 at collector 1 potential F2 at collector 2 potential

CONTROLLING DIMENSIONS IN MILLIMETRES APPROX. CONVERTED DIMENSIONS IN INCHES

MLP832 PACKAGE DIMENSIONS

	MILLIN	IETRES	INC	HES	MILLIME		IETRES	INC	HES
DIM	MIN.	MAX.	MIN.	MAX.	DIM	MIN.	MAX.	MIN.	MAX.
Α	0.80	1.00	0.031	0.039	е	0.65	REF	0.025	6 BSC
A1	0.00	0.05	0.00	0.002	E	2.00	BSC	0.0787	7 BSC
A2	0.65	0.75	0.0255	0.0295	E2	0.43	0.63	0.017	0.0249
А3	0.15	0.25	0.006	0.0098	E4	0.16	0.36	0.006	0.014
b	0.24	0.34	0.009	0.013	L	0.20	0.45	0.0078	0.0157
b1	0.17	0.30	0.0066	0.0118	L2		0.125	0.00	0.005
D	3.00	BSC	0.118	BSC	r	0.075	BSC	0.002	9 BSC
D2	0.82	1.02	0.032	0.040	θ	0°	12°	0°	12°
D3	1.01	1.21	0.0397	0.0476					

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